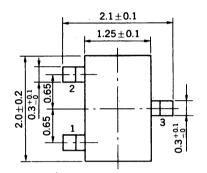


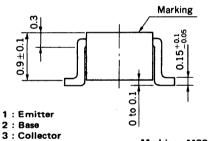
SILICON TRANSISTOR GN1A4M

MEDIUM SPEED SWITCHING RESISTOR BUILT-IN TYPE PNP TRANSISTOR

PACKAGE DIMENSIONS

in millimeters

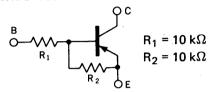




Marking: M33

FEATURES

• Resistors Built-in TYPE



Complementary to GA1A4M

ABSOLUTE MAXIMUM RATINGS

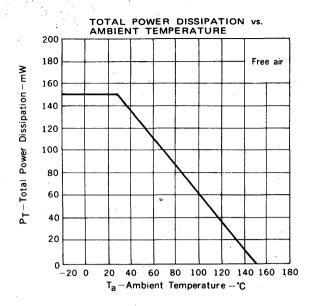
Maximum Voltages and Currents (Ta = 25	°C)		
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-50	٧
Emitter to Base Voltage	V_{EBO}	-10	٧
Collector Current (DC)	I _{C(DC)}	-100	mΑ
Collector Current (Pulse)	I _{C(Pulse)}	-200	mΑ
Maximum Power Dissipation			
Total Power Dissipation			
at 25 °C Ambient Temperature	P_T	150	mW
Maximum Temperatures			
Junction Temperature	Ti	150	°C
Storage Temperature Range	Tera	-55 to +150	°C

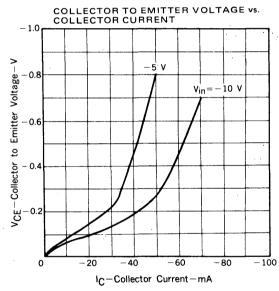
ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

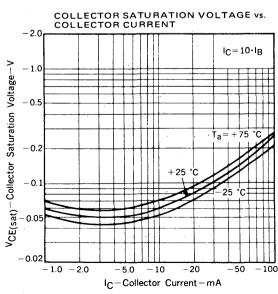
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Cutoff Current	ІСВО			-100	nA	V _{CB} = -50 V, I _E = 0	
DC Current Gain	hFE1*	35	60	100		$V_{CB} = -5.0 \text{ V, } I_{C} = -5.0 \text{ mA}$	
DC Current Gain	hFE2*	80	200			$V_{CE} = -5.0 \text{ V, I}_{C} = -50 \text{ mA}$	
Collector Saturation Voltage	V _{CE(sat)} *		-0.04	-0.2	٧	$I_C = -50 \text{ mA}, I_B = -0.25 \text{ mA}$	
Low-Level Input Voltage	VIL*		-1.13	-0.8	V	$V_{CE} = -5.0 \text{ V, I}_{C} = -100 \mu\text{A}$	
High-Level Input Voltage	VIH*	-3.0	-1.6		V	$V_{CE} = -0.2 \text{ V, I}_{C} = -5.0 \text{ mA}$	
Input Resistor	R ₁	7	10	13	kΩ		
Resistor Ratio	R ₁ /R ₂	0.9	1.0	1.1			
Turn-on Time	ton		0.1	0.5	μs	$V_{CC} = -5 \text{ V}, V_{in} = -5 \text{ V}$ $R_L = 1 \text{ k}\Omega$	
Storage Time	t _{stg}		0.95	3.0	μs		
Turn-off Time	toff		1.1	5.0	μs	PW = 2 μs, Duty Cycle ≤ 2 %	

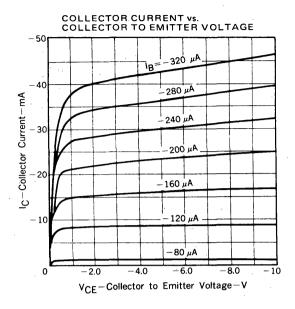
^{*} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

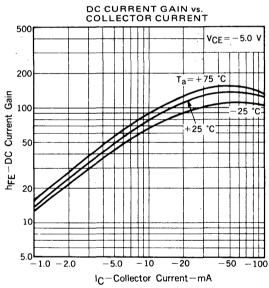
TYPICAL CHARACTERISTICS (Ta = 25 °C)

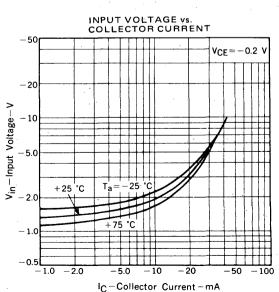


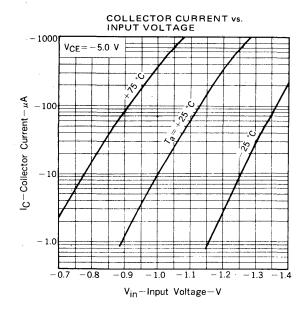


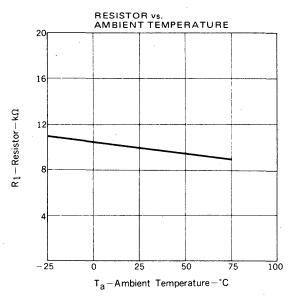


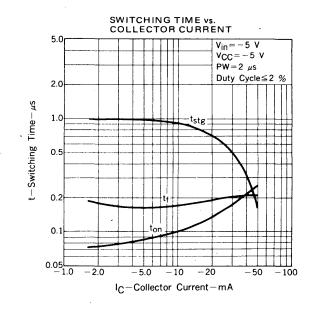












GN1A4M

NEC ELECTRON DEVICE